

UN4121/4122/4123/4124/412X/412Y

Silicon PNP epitaxial planer transistor

For digital circuits

■ Features

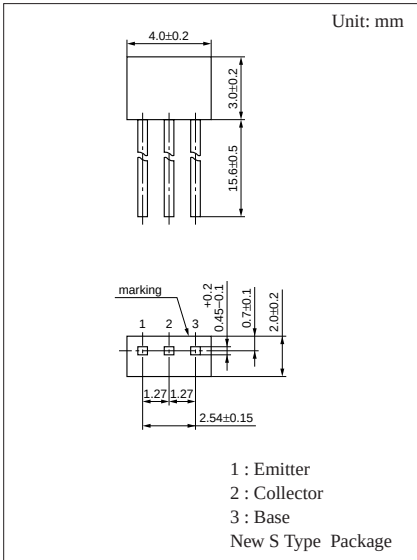
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.
- New S type package, allowing supply with the radial taping.

■ Resistance by Part Number

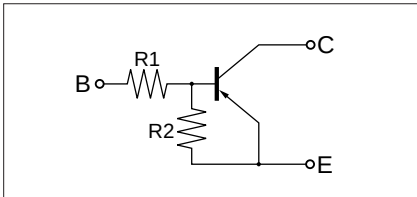
	(R ₁)	(R ₂)
• UN4121	2.2kΩ	2.2kΩ
• UN4122	4.7kΩ	4.7kΩ
• UN4123	10kΩ	10kΩ
• UN4124	2.2kΩ	10kΩ
• UN412X	0.27kΩ	5.0kΩ
• UN412Y	3.1kΩ	4.6kΩ

■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	-50	V
Collector to emitter voltage	V _{CEO}	-50	V
Collector current	I _C	-500	mA
Total power dissipation	P _T	300	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C



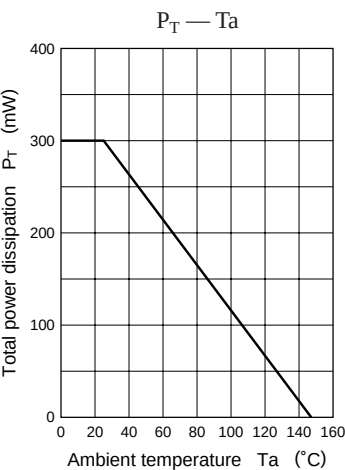
Internal Connection



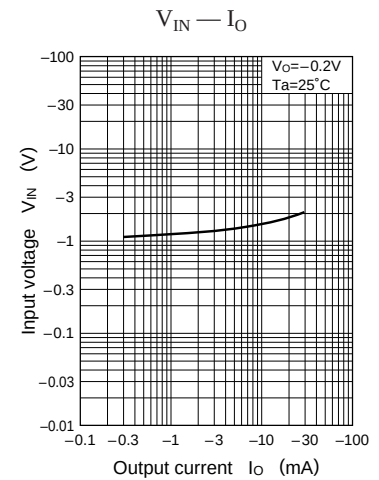
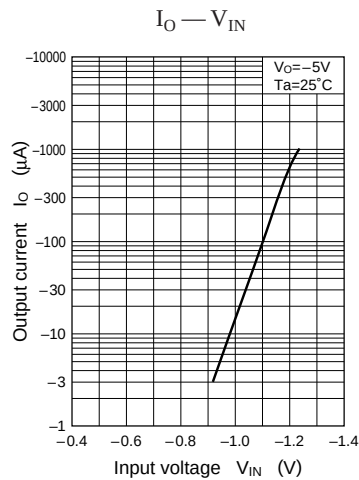
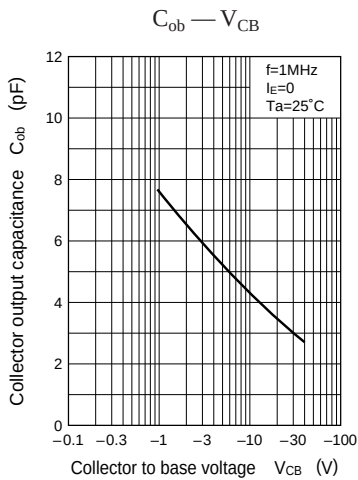
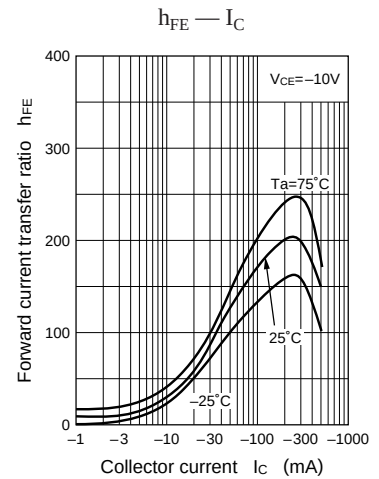
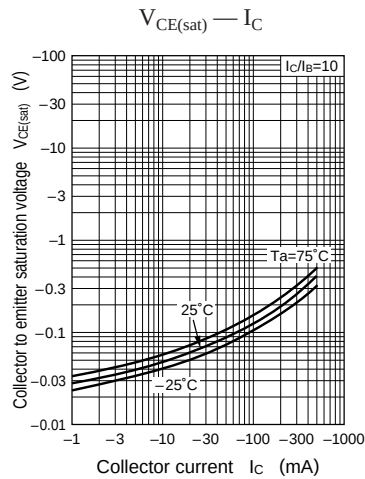
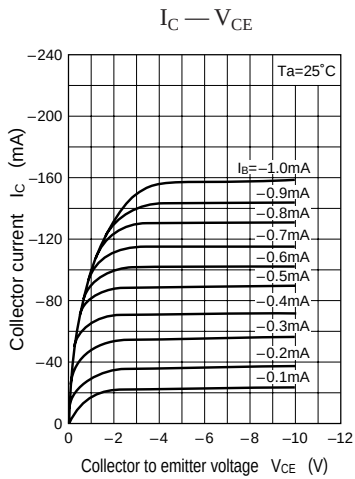
■ Electrical Characteristics (Ta=25°C)

Parameter		Symbol	Conditions	min	typ	max	Unit	
Collector cutoff current		I_{CBO}	$V_{CB} = -50V, I_E = 0$			-1	μA	
		UN412X	I_{CBO}	$V_{CB} = -50V, I_E = 0$		-0.1		
Collector cutoff current		I_{CEO}	$V_{CE} = -50V, I_B = 0$			-1	μA	
		UN412X	I_{CEO}	$V_{CE} = -50V, I_B = 0$		-0.5		
Emitter cutoff current	UN4121	I_{EBO}	$V_{EB} = -6V, I_C = 0$			-5	mA	
	UN4122/412X/412Y					-2		
	UN4123/4124					-1		
Collector to base voltage		V_{CBO}	$I_C = -10\mu A, I_E = 0$	-50			V	
Collector to emitter voltage		V_{CEO}	$I_C = -2mA, I_B = 0$	-50			V	
Forward current transfer ratio	UN4121	h_{FE}	$V_{CE} = -10V, I_C = -100mA$	40				
	UN4122/412Y			50				
	UN4123/4124			60				
	UN412X			20				
Collector to emitter saturation voltage		$V_{CE(sat)}$	$I_C = -100mA, I_B = -5mA$			-0.25	V	
		UN412X	$V_{CE(sat)}$	$I_C = -10mA, I_B = -0.3mA$		-0.25		
		UN412Y	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$		-0.15		
Output voltage high level		V_{OH}	$V_{CC} = -5V, V_B = -0.5V, R_L = 500\Omega$	-4.9			V	
Output voltage low level		V_{OL}	$V_{CC} = -5V, V_B = -3.5V, R_L = 500\Omega$			-0.2	V	
Transition frequency		f_T	$V_{CB} = -10V, I_E = 50mA, f = 200MHz$		80		MHz	
Input resistance	UN4121/4124	R_1		(-30%)	2.2	(+30%)	$k\Omega$	
	UN4122				4.7			
	UN4123				10			
	UN412X				0.27			
	UN412Y				3.1			
Resistance ratio		R_1/R_2		0.8	1.0	1.2		
				UN4124	0.17	0.22		0.27
				UN412X	0.043	0.054		0.065
				UN412Y		0.67		

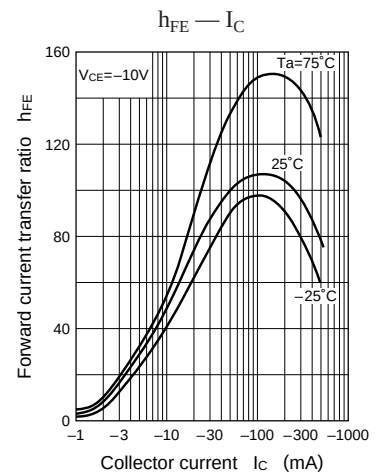
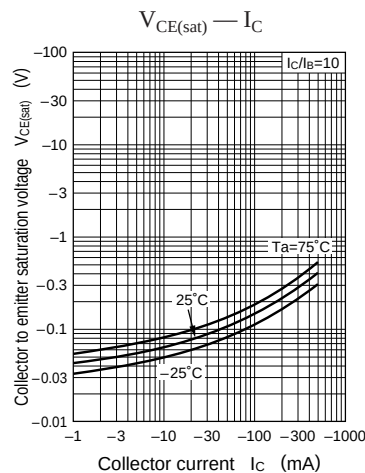
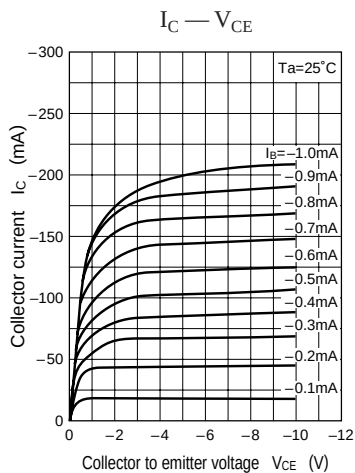
Common characteristics chart

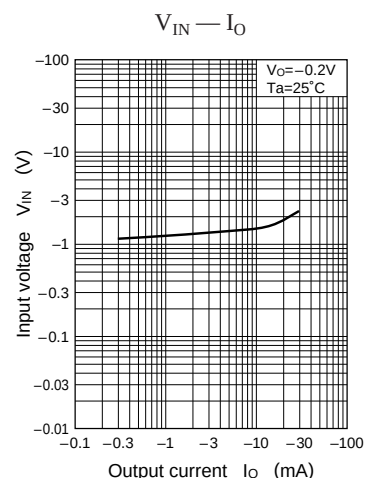
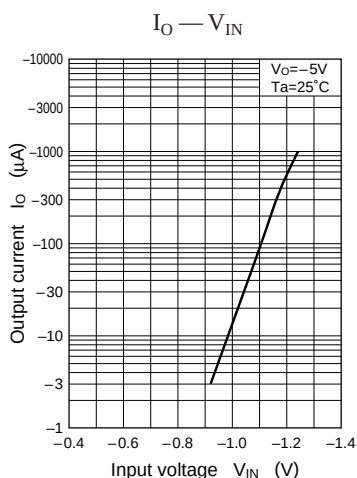
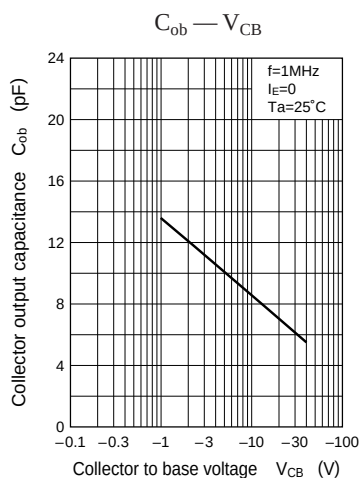


Characteristics charts of UN4121

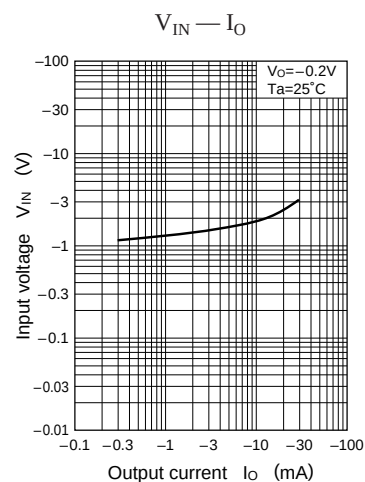
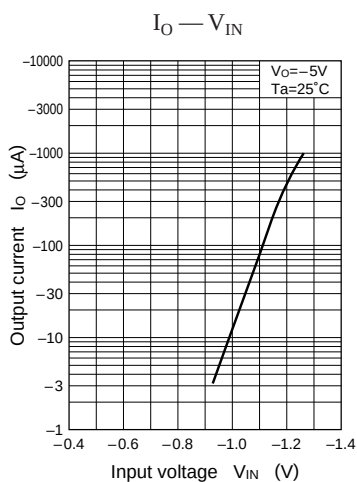
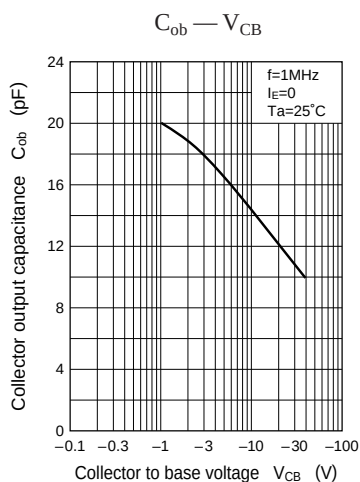
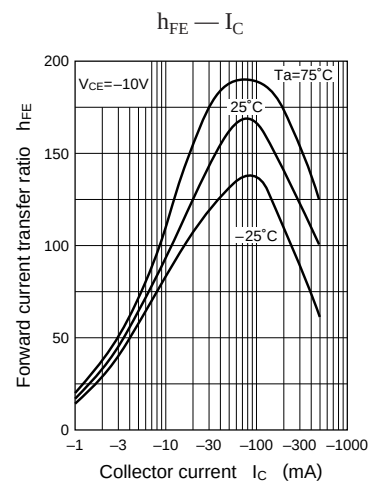
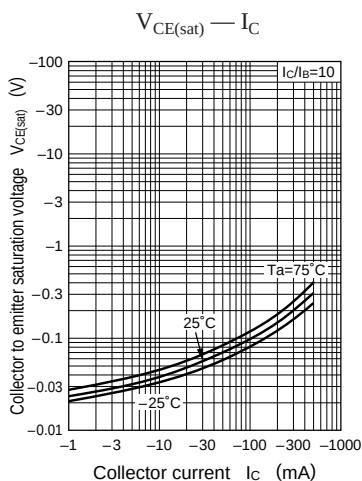
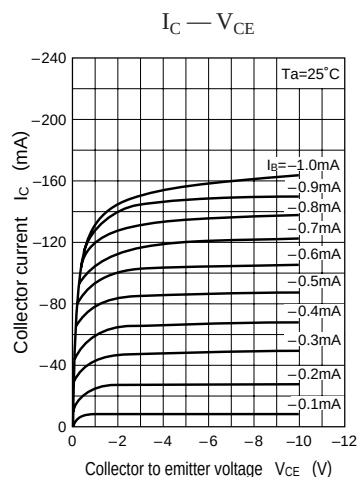


Characteristics charts of UN4122

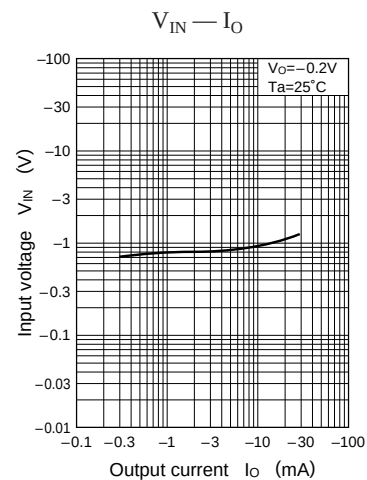
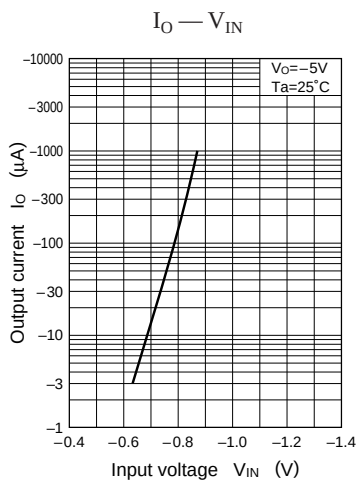
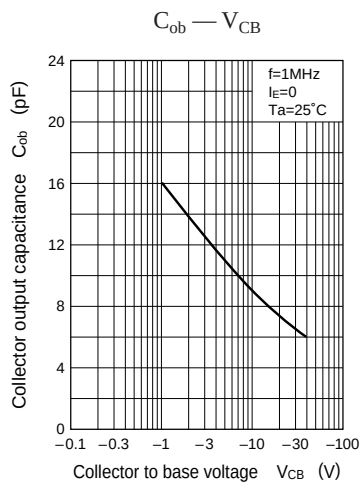
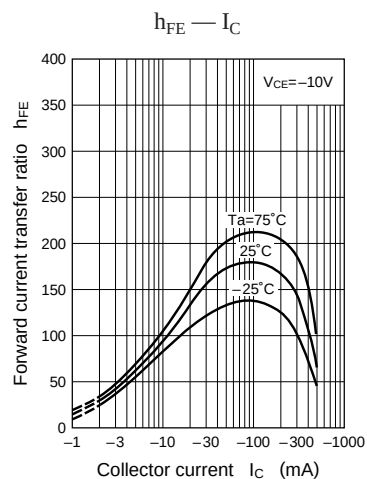
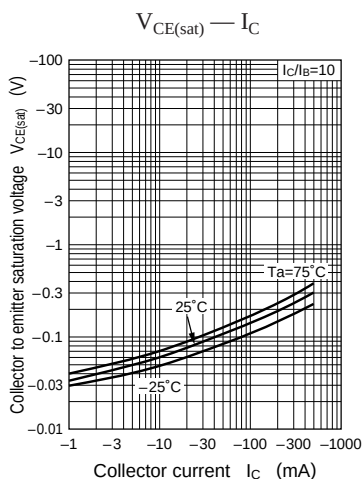
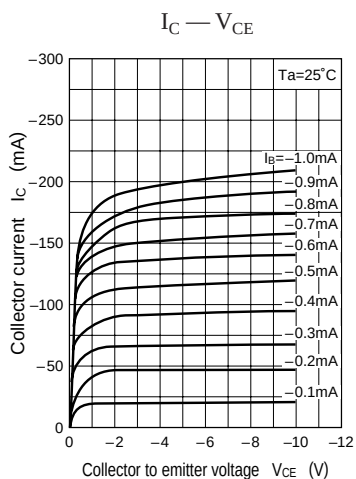




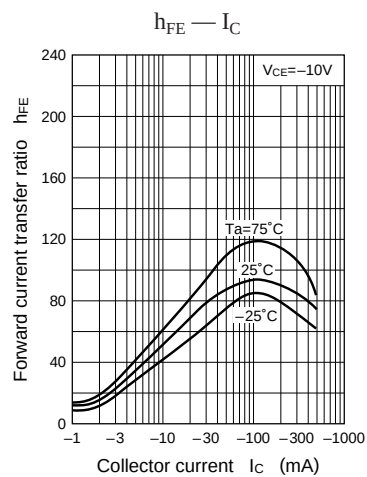
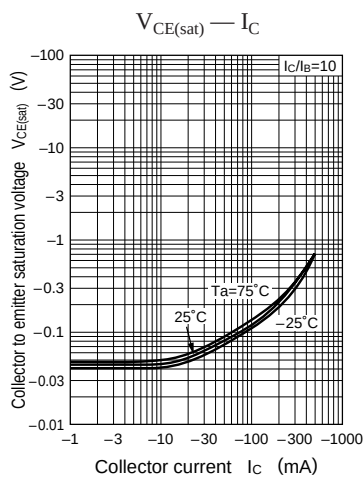
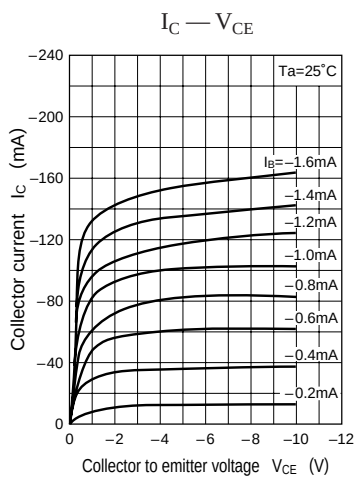
Characteristics charts of UN4123

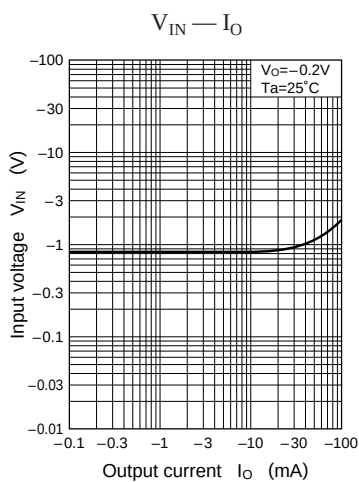
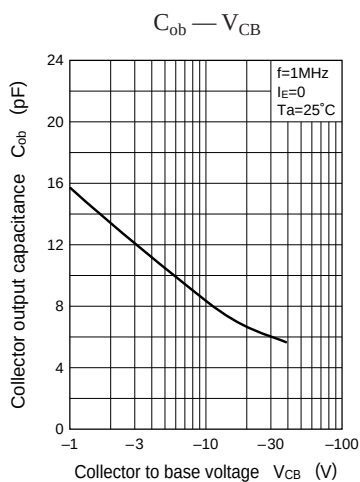


Characteristics charts of UN4124



Characteristics charts of UN412X





Characteristics charts of UN412Y

